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# **State-of-the-Art Program on Compound Semiconductors 45 (SOTAPOCS 45) -and- Wide Bandgap Semiconductor Materials and Devices 7**

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## **Editors:**

### **F. Ren**

University of Florida  
Gainesville, Florida, USA

### **J. A. Bardwell**

Institute for Microstructural Sciences  
Ottawa, Ontario, Canada

### **W. Johnson**

Nirtonex Corporation  
Raleigh, North Carolina, USA

### **E. B. Stokes**

University of North Carolina  
Charlotte, North Carolina, USA

### **P. C. Chang**

Northrop Grumman  
Redondo Beach, California, USA

### **P. H. Shen**

US Army Research Lab  
Adelphi, Maryland, USA

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